

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Peter Rabkin et al.

Application No.:

Filed: Herewith

For: TRANSISTOR AND MEMORY
CELL WITH ULTRA-SHORT GATE
FEATURE AND METHOD OF
FABRICATING THE SAME

Examiner: To be Assigned

Art Unit: To be Assigned

PRELIMINARY AMENDMENT

March 13, 2001

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination of the above-referenced application, please enter the following amendments and remarks.

IN THE TITLE:

Please change the Title of the invention to:

--TRANSISTOR WITH ULTRA-SHORT GATE FEATURE AND METHOD OF
FABRICATING THE SAME--.

IN THE SPECIFICATION:

At page 1, line 4, please add the following new heading and paragraph:

--CROSS-REFERENCES TO RELATED APPLICATIONS

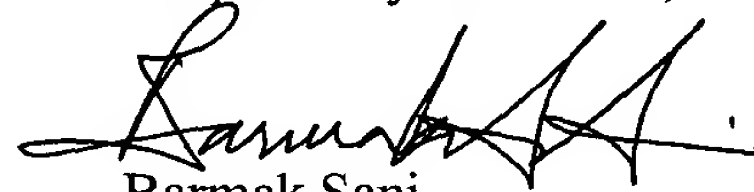
This is a Division of U.S. Application No. 09/797,863 (Atty. Docket No. 00939A-079300US), filed March 1, 2001, and entitled "Transistor and Memory Cell with Ultra-Short Gate Feature and Method of Fabricating the Same", the disclosure of which is incorporated herein by reference.--

IN THE CLAIMS:

Please cancel claims 19-76 and 90-99.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 650-326-2400.

Respectfully submitted,



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